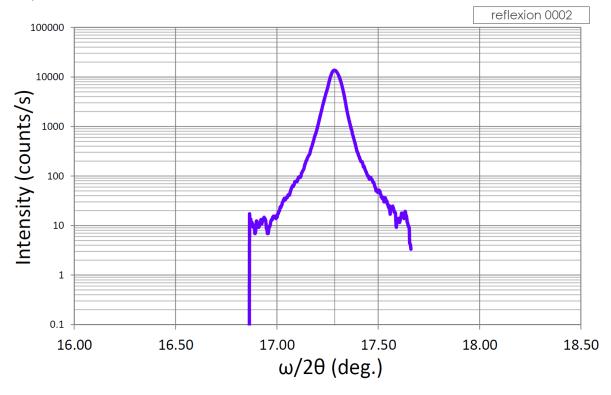
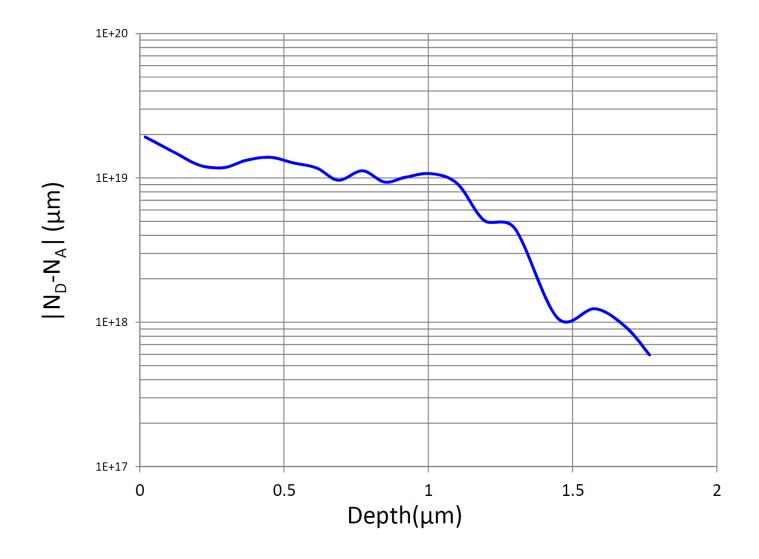
X-Ray Diffraction

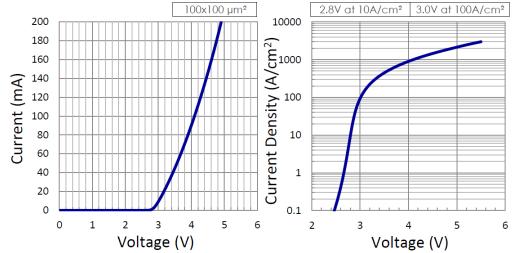


Peak	InGaN QW	GaN	AlGaN barrier	AlGaN
Diffraction Angle	17.285 °			
Intensity	1375,0			
FWHM	252 "			

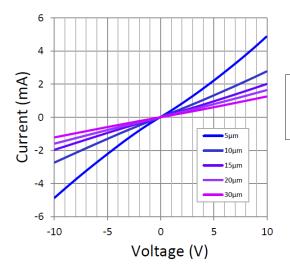
	InGaN QW
In content	-
QW thickness	-
barrier thickness	-



I-V Characteristics



P-GaN Electrical Properties (TLM)



Sheet Resistance Rs = 24351 Ω/\Box Contact Resistance Rc = 3E-03 $\Omega.cm^2$ P-GaN resistivity ρ = 0.37 $\Omega.cm$

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